

**APPENDIX A**  
**"CLEAN" VERSION OF EACH PARAGRAPH/SECTION/CLAIM**  
**37 C.F.R. § 1.121(b)(ii) AND (c)(i)**

**CLAIMS (with indication of amended or new):**

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Q 1. (Thrice Amended) A semiconductor device comprising, in combination, a silicon substrate having a first and second surface; a first layer disposed on said first surface and having impurities of the n or p conductivity type uniformly distributed throughout the volume of said first layer; a second layer disposed on said first layer; said second layer having impurities of the same type as those in said first layer uniformly distributed therethrough and having a substantially uniform resistivity; the concentration of impurities in said second layer being greater than the concentration of impurities in said first layer; a plurality of diffusions of a conductivity type opposite to that of said second layer uniformly distributed into the surface of said second layer and defining p-n junctions therein; and said first layer and said second layer being epitaxial silicon layers.

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